Silicon phototransistors

TYPE NO.	P_D @ $T_A = 25^\circ C$	I_C max.	BV_{CBO} min.	LV_{CEO} min.	I_L @ V_{CE} @ H min.	I_D @ V_{CE} max.	t_r max.	t_f max.	CASE
MAL 100	200mW	50mA	50V	30V	0.20mA @ 5V @ $20Wm^{-2}$	100nA @ 5V	4.0μs	5.0μs	PD-37
MEL 31	200mW	—	40V	30V	0.01mA @ 5V @ $20Wm^{-2}$	50nA @ 5V	—	—	TO-106
MEL 32	200mW	—	60V	40V	0.03mA @ 5V @ $20Wm^{-2}$	50nA @ 5V	—	—	TO-106
MEL 100	200mW	50mA	50V	30V	0.20mA @ 5V @ $20Wm^{-2}$	100nA @ 5V	4.0μs	5.0μs	TO-106
MEPT 100	200mW	25mA	50V	30V	0.20mA @ 5V @ $50Wm^{-2}$	100nA @ 5V	2.8μs	2.8μs	TO-106
MEPT 100A	200mW	25mA	50V	30V	1.00mA @ 5V @ $50Wm^{-2}$	100nA @ 5V	2.8μs	2.8μs	TO-106
MEPT 100B	200mW	25mA	50V	30V	1.30mA @ 5V @ $50Wm^{-2}$	100nA @ 5V	2.8μs	2.8μs	TO-106